

SI2307DS-T1-GE3 Datasheet

P-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω) Typ.	I _D (A) ^a	Q _g (Typ.)
- 30	0.046 at V _{GS} = - 10 V	- 5.6	11.4 nC
	0.049 at V _{GS} = - 6 V	- 5	
	0.054 at V _{GS} = - 4.5 V	-4.5	

FEATURES

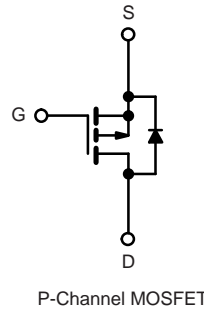
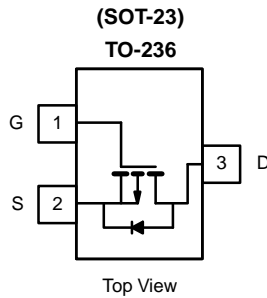
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- For Mobile Computing
 - Load Switch
 - Notebook Adaptor Switch
 - DC/DC Converter



ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	- 30	V	
Gate-Source Voltage	V _{GS}	± 20		
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	- 5.6	A
		T _C = 70 °C	- 5.1	
		T _A = 25 °C	- 5.4 ^{b,c}	
		T _A = 70 °C	- 4.3 ^{b,c}	
Pulsed Drain Current (t = 100 μs)	I _{DM}	- 18		
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	- 2.1	
		T _A = 25 °C	- 1 ^{b,c}	
Maximum Power Dissipation	P _D	T _C = 25 °C	2.5	W
		T _C = 70 °C	1.6	
		T _A = 25 °C	1.25 ^{b,c}	
		T _A = 70 °C	0.8 ^{b,c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b,d}	R _{thJA}	75	100	°C/W	
Maximum Junction-to-Foot (Drain)	R _{thJF}	40	50		

Notes:

- Based on T_C = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 5 s.
- Maximum under steady state conditions is 166 °C/W.

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		-19		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		4			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.5		-2.0	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			-5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}, V_{GS} = -10\text{ V}$	-2.5			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -4.4\text{ A}$		0.046		Ω
		$V_{GS} = -6\text{ V}, I_D = -4\text{ A}$		0.049		
		$V_{GS} = -4.5\text{ V}, I_D = -3.6\text{ A}$		0.054		
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}, I_D = -3.4\text{ A}$		18		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1295		pF
Output Capacitance	C_{oss}		150			
Reverse Transfer Capacitance	C_{rss}		130			
Total Gate Charge	Q_g	$V_{DS} = -15\text{ V}, V_{GS} = -10\text{ V}, I_D = -5.4\text{ A}$		24	36	nC
		$V_{DS} = -15\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -5.4\text{ A}$		11.4	17	
Gate-Source Charge	Q_{gs}	$V_{DS} = -15\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -5.4\text{ A}$		3.4		
Gate-Drain Charge	Q_{gd}			3.8		
Gate Resistance	R_g	$f = 1\text{ MHz}$	1.5	7.7	15.4	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 3.5\text{ }\Omega$ $I_D \cong -4.3\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$		13	20	ns
Rise Time	t_r		4	8		
Turn-Off Delay Time	$t_{d(off)}$		38	57		
Fall Time	t_f		6	12		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 3.5\text{ }\Omega$ $I_D \cong -4.3\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		28	42	
Rise Time	t_r		16	24		
Turn-Off Delay Time	$t_{d(off)}$		30	45		
Fall Time	t_f		10	20		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			-2.1	A
Pulse Diode Forward Current ($t = 100\text{ }\mu\text{s}$)	I_{SM}				-80	
Body Diode Voltage	V_{SD}	$I_S = -4.3\text{ A}, V_{GS} = 0\text{ V}$		-0.8	-1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -4.3\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		15	23	ns
Body Diode Reverse Recovery Charge	Q_{rr}		7	14	nC	
Reverse Recovery Fall Time	t_a		8		ns	
Reverse Recovery Rise Time	t_b		7			

Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Output Characteristics



Transfer Characteristics



On-Resistance vs. Drain Current



Capacitance



Gate Charge



On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

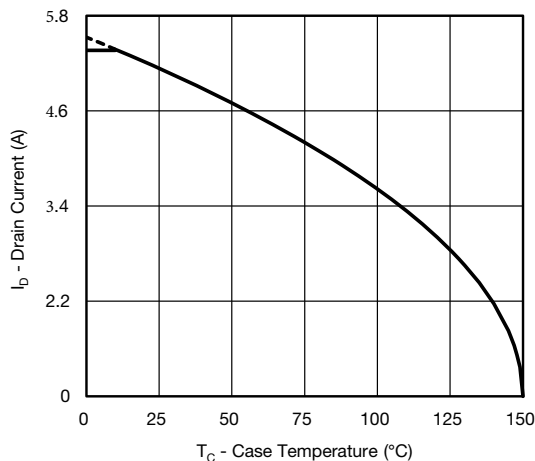


Single Pulse Power (Junction-to-Ambient)

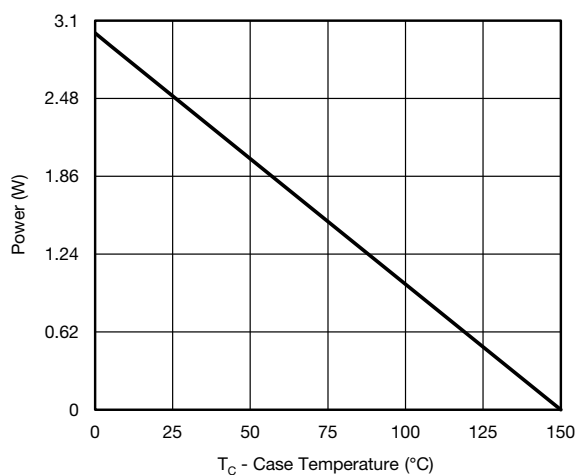


Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



Power, Junction-to-Foot



Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

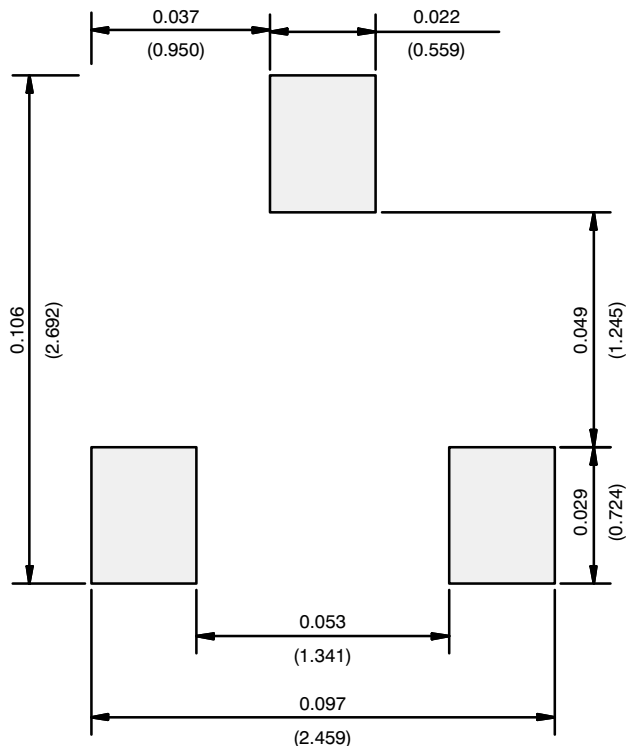
SOT-23 (TO-236): 3-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A ₁	0.01	0.10	0.0004	0.004
A ₂	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E ₁	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e ₁	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L ₁	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°

ECN: S-03946-Rev. K, 09-Jul-01
DWG: 5479

RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads
Dimensions in Inches/(mm)

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